

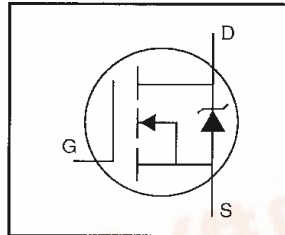
# International IR Rectifier

PD - 95452

## IRL530PbF

### HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$  Specified at  $V_{GS}=4V$  &  $5V$
- $175^{\circ}C$  Operating Temperature
- Fast Switching
- Ease of Paralleling
- Lead-Free



$$V_{DSS} = 100V$$

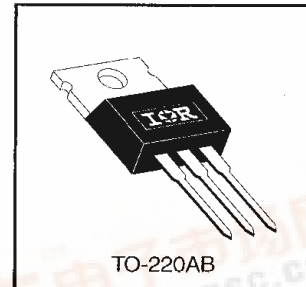
$$R_{DS(on)} = 0.16\Omega$$

$$I_D = 15A$$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



### Absolute Maximum Ratings

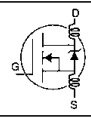
	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	15	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	11	
$I_{DM}$	Pulsed Drain Current ①	60	
$P_D @ T_C = 25^{\circ}C$	Power Dissipation	88	W
	Linear Derating Factor	0.59	W/ $^{\circ}C$
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	290	mJ
$I_{AR}$	Avalanche Current ①	15	A
$E_{AR}$	Repetitive Avalanche Energy ①	8.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}C$
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	---	1.7	$^{\circ}C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	---	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient	---	---	62	



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

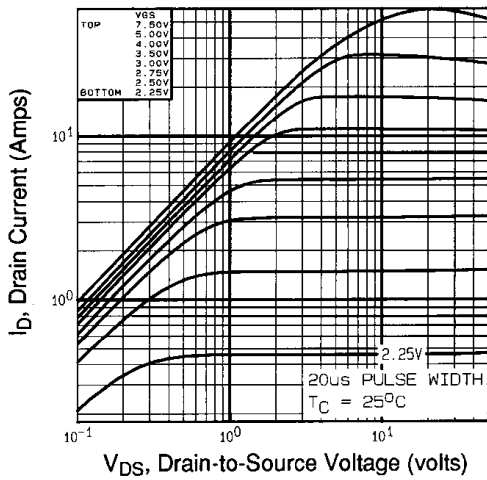
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	100	—	—	V	V <sub>GS</sub> =0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.14	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.16	Ω	V <sub>GS</sub> =5.0V, I <sub>D</sub> =9.0A ④
		—	—	0.22		V <sub>GS</sub> =4.0V, I <sub>D</sub> =7.5A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	2.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	6.4	—	—	S	V <sub>DS</sub> =50V, I <sub>D</sub> =9.0A ④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V
		—	—	250		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> =10V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> =-10V
Q <sub>g</sub>	Total Gate Charge	—	—	28	nC	I <sub>D</sub> =15A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	3.8		V <sub>DS</sub> =80V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	14		V <sub>GS</sub> =5.0V See Fig. 6 and 13 ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	4.7	—	ns	V <sub>DD</sub> =50V
t <sub>r</sub>	Rise Time	—	100	—		I <sub>D</sub> =15A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	22	—		R <sub>G</sub> =12Ω
t <sub>f</sub>	Fall Time	—	48	—		R <sub>D</sub> =32Ω See Figure 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	930	—	pF	V <sub>GS</sub> =0V
C <sub>oss</sub>	Output Capacitance	—	250	—		V <sub>DS</sub> =25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	57	—		f=1.0MHz See Figure 5

## Source-Drain Ratings and Characteristics

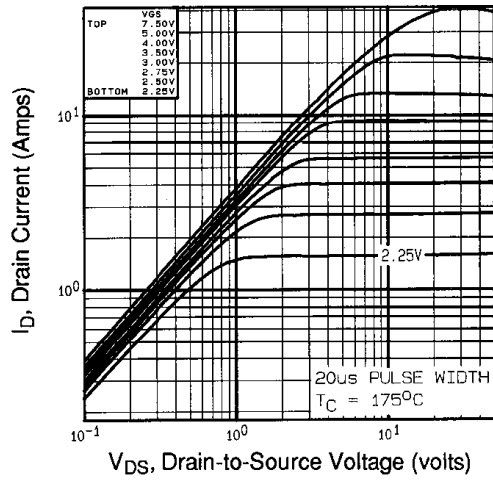
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	15	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	60		
V <sub>SD</sub>	Diode Forward Voltage	—	—	2.5	V	T <sub>J</sub> =25°C, I <sub>S</sub> =15A, V <sub>GS</sub> =0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	150	200	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =15A
Q <sub>rr</sub>	Reverse Recovery Charge	—	0.93	1.4	μC	di/dt=100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

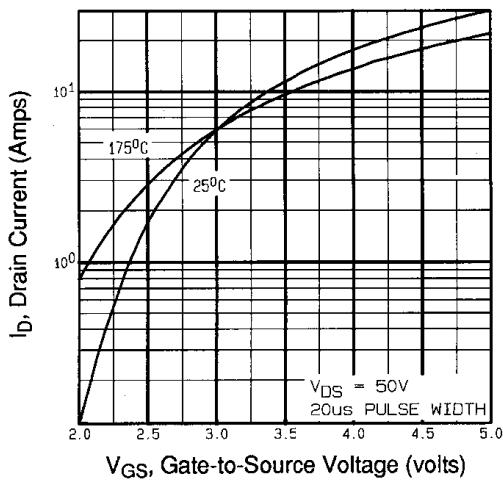
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② V<sub>DD</sub>=25V, starting T<sub>J</sub>=25°C, L=1.9mH  
R<sub>G</sub>=25Ω, I<sub>AS</sub>=15A (See Figure 12)
- ③ I<sub>SD</sub>≤15A, di/dt≤140A/μs, V<sub>DD</sub>≤V<sub>(BR)DSS</sub>,  
T<sub>J</sub>≤175°C
- ④ Pulse width ≤ 300 μs; duty cycle ≤2%.



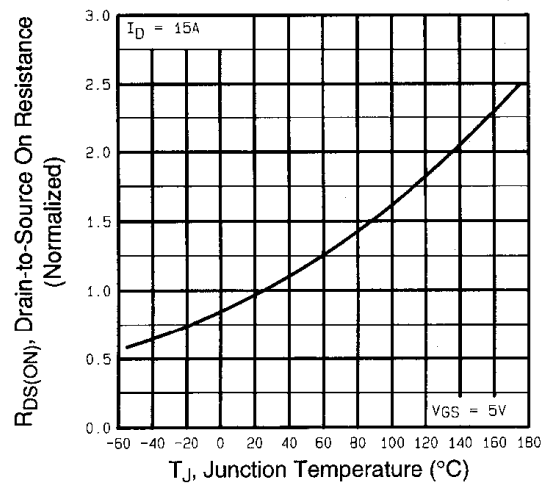
**Fig 1.** Typical Output Characteristics,  
 $T_C=25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  
 $T_C=175^\circ\text{C}$

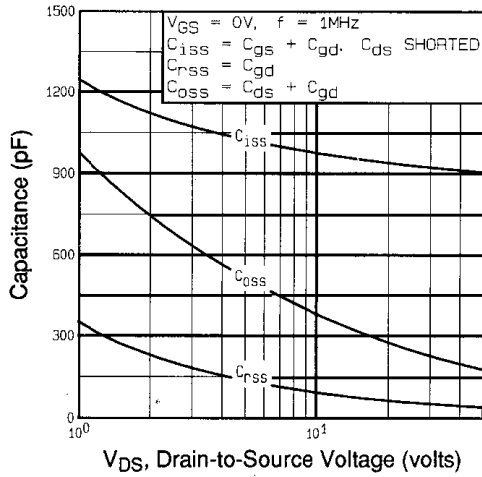


**Fig 3.** Typical Transfer Characteristics

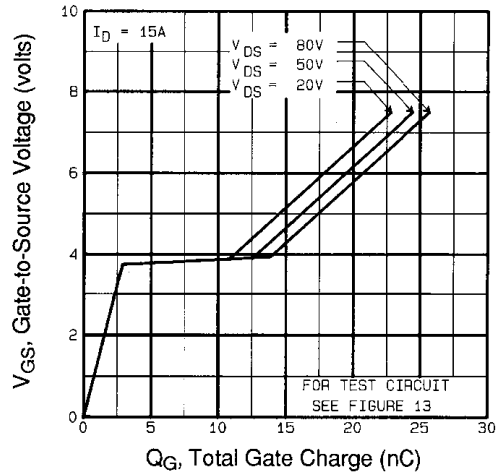


**Fig 4.** Normalized On-Resistance  
Vs. Temperature

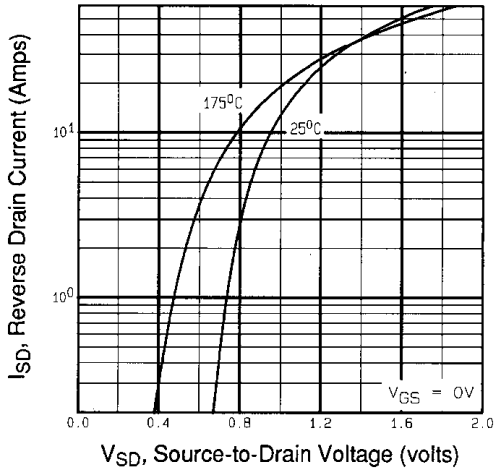
# IRL530PbF



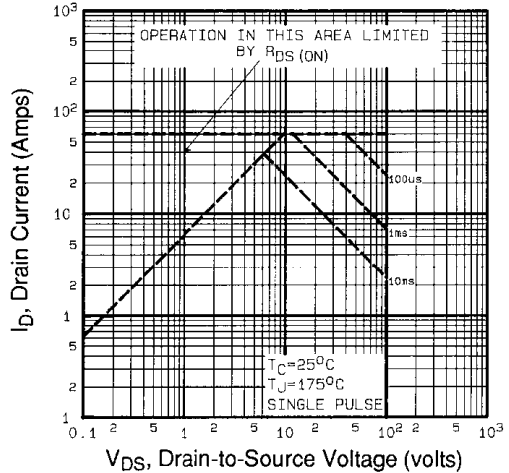
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

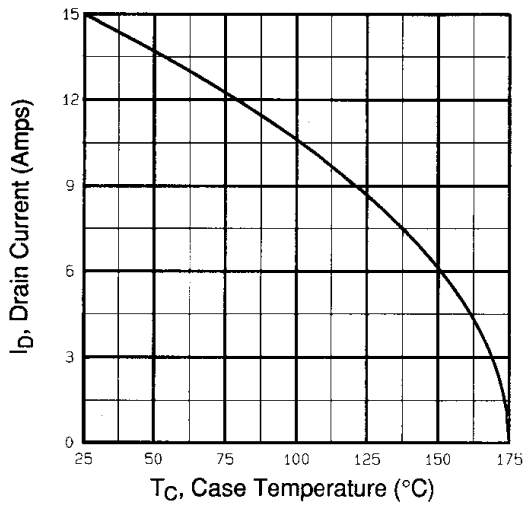


Fig 9. Maximum Drain Current Vs. Case Temperature

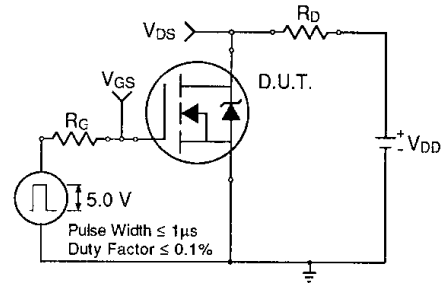


Fig 10a. Switching Time Test Circuit

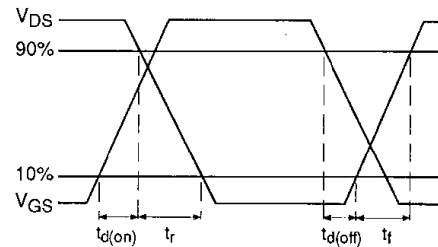


Fig 10b. Switching Time Waveforms

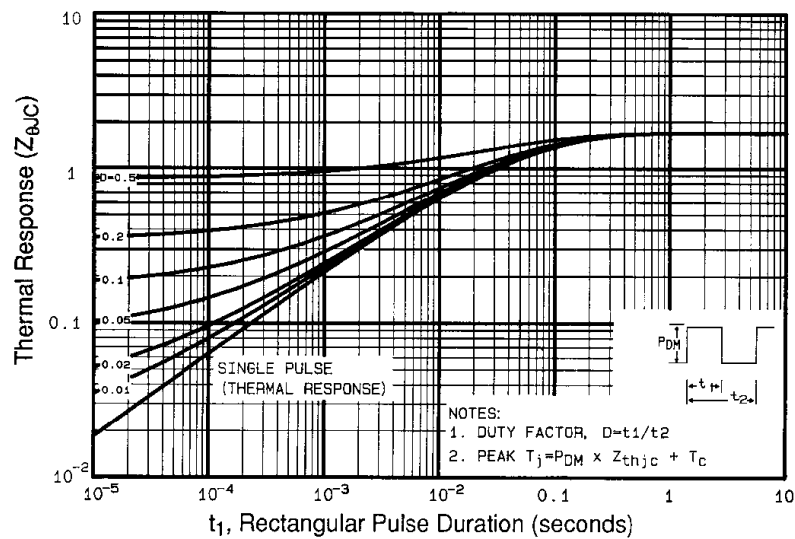
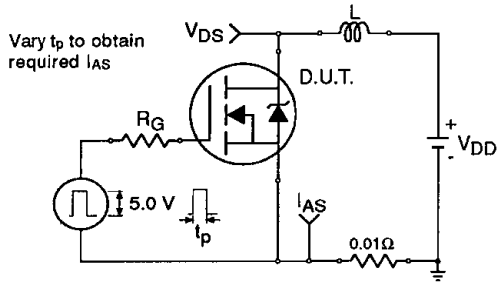
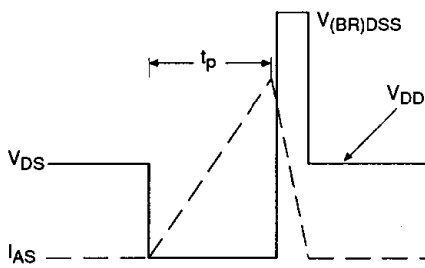


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

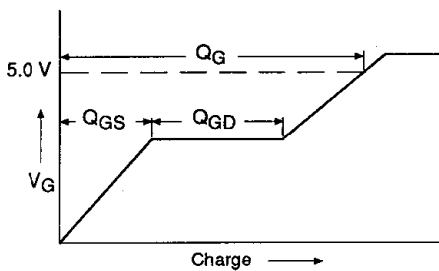
# IRL530PbF



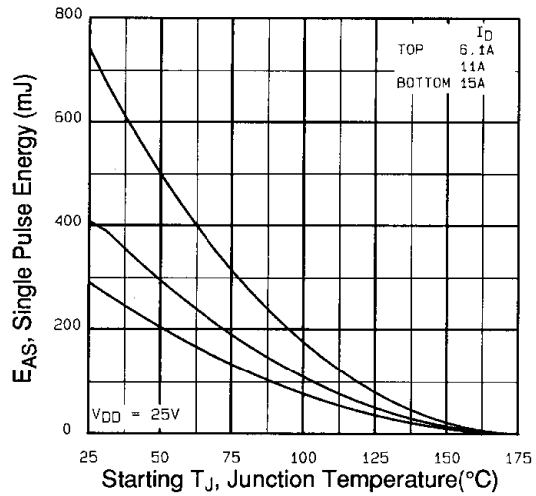
**Fig 12a.** Unclamped Inductive Test Circuit



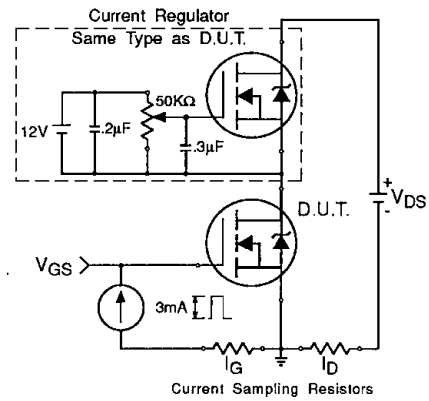
**Fig 12b.** Unclamped Inductive Waveforms



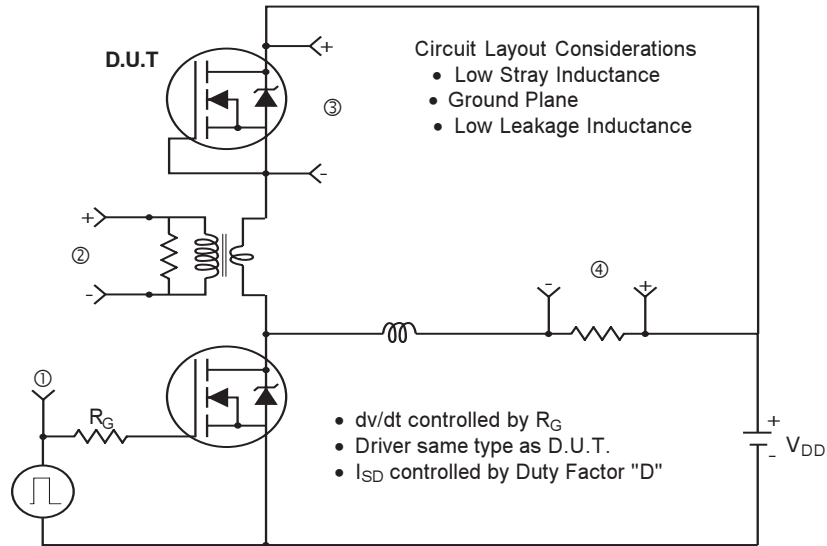
**Fig 13a.** Basic Gate Charge Waveform



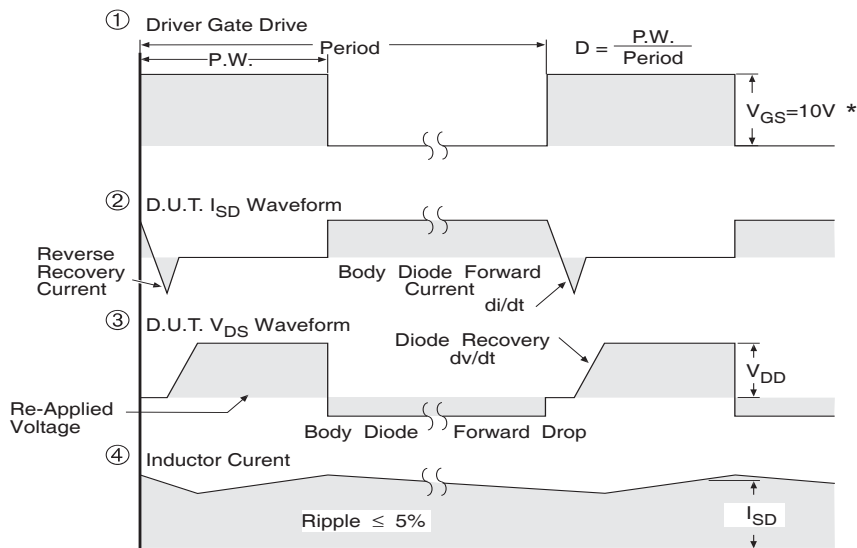
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit



**Fig. 14. Peak Diode Recovery  $dv/dt$  Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

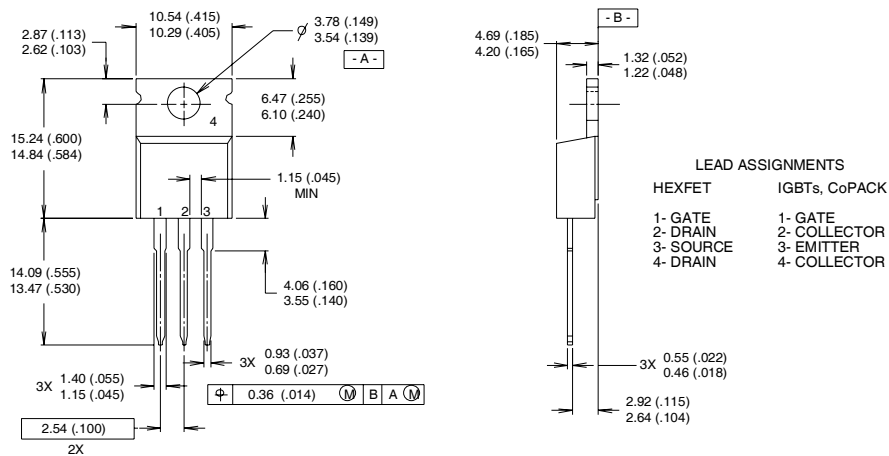
**Fig 15. For N-Channel Power MOSFETs**

# IRL530PbF

International  
**IR** Rectifier

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

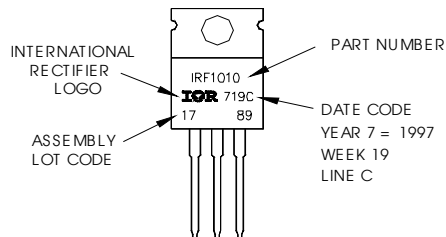


**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
**IR** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
 TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.06/04

[www.irf.com](http://www.irf.com)